

Silicon PNP Power Transistors

2SA1220 2SA1220A

DESCRIPTION

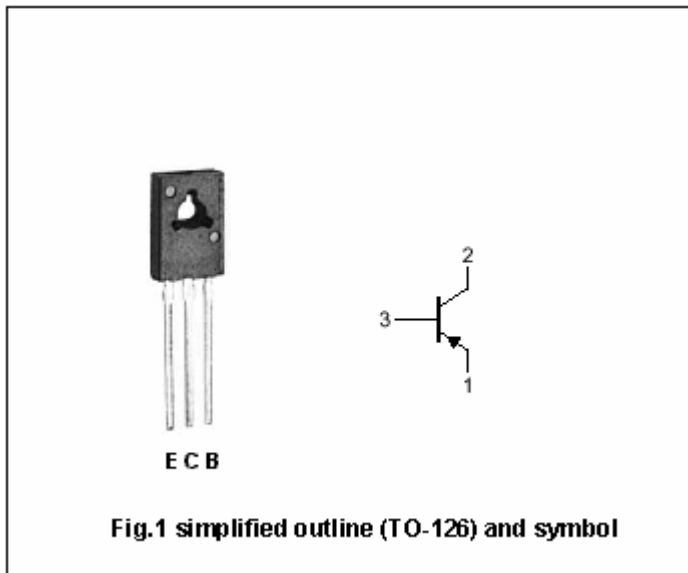
- With TO-126 package
- Complement to type 2SC2690/2690A

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA1220	-120	V
		2SA1220A	-160	
V _{CEO}	Collector-emitter voltage	2SA1220	-120	V
		2SA1220A	-160	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.2	A
I _{CM}	Collector current-peak		-2.5	A
I _B	Base current		-0.3	A
P _D	Total power dissipation	T _a =25°C	1.2	W
		T _C =25°C	20	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55°C+150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.2A			-0.7	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A; I _B =-0.2A			-1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-5mA; V _{CE} =-5V	35			
h _{FE-2}	DC current gain	I _C =-0.3A; V _{CE} =-5V	60		320	
C _{ob}	Output capacitance	I _E =0; V _{CB} =-10V f=1MHz		26		pF
f _T	Transition frequency	I _C =-0.2A; V _{CE} =5V		175		MHz

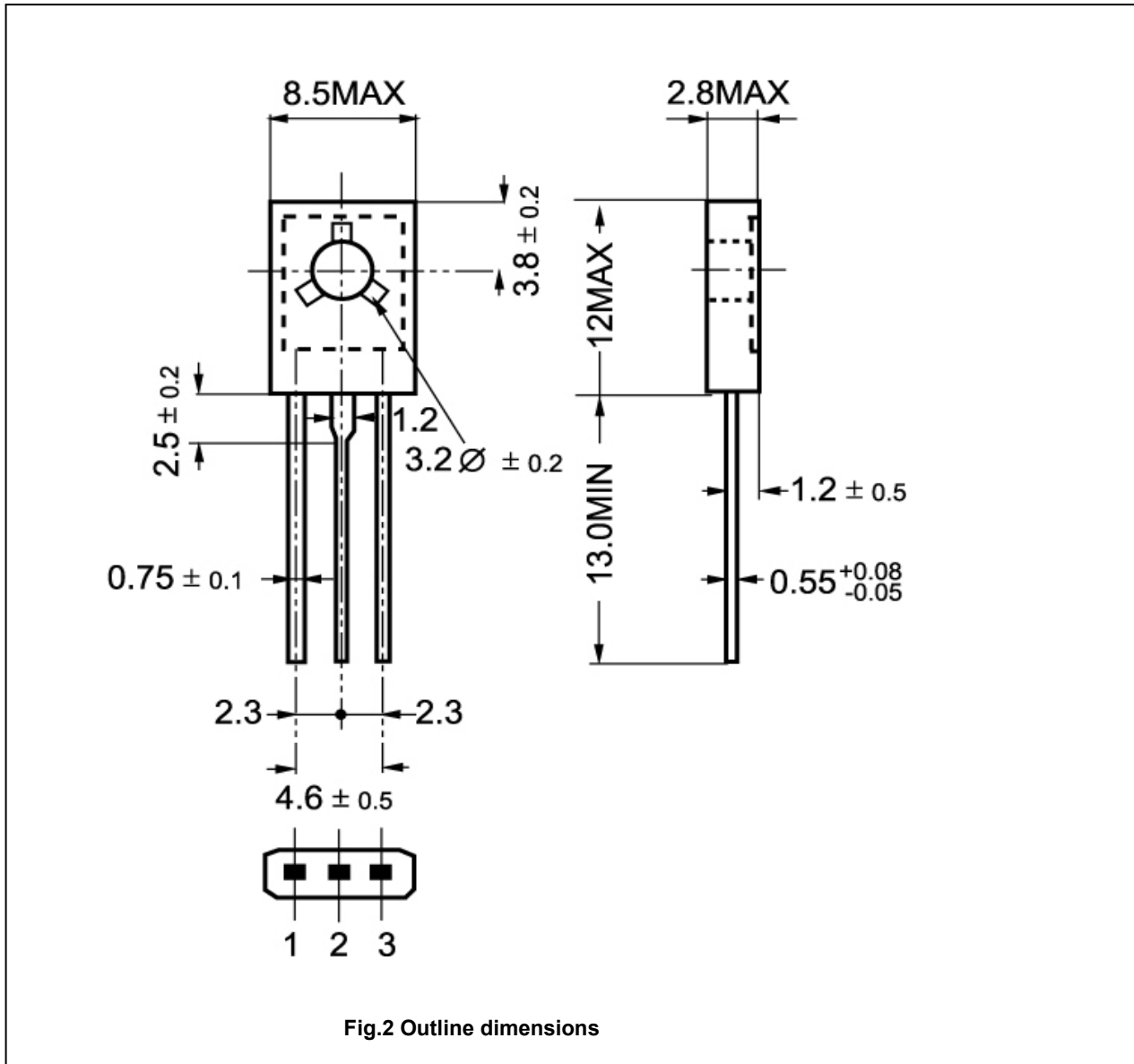
◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



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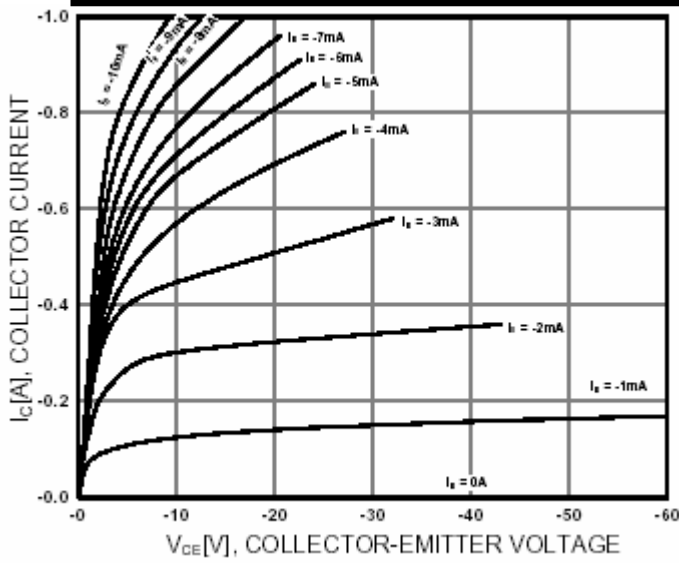


Fig.3 Static Characteristic

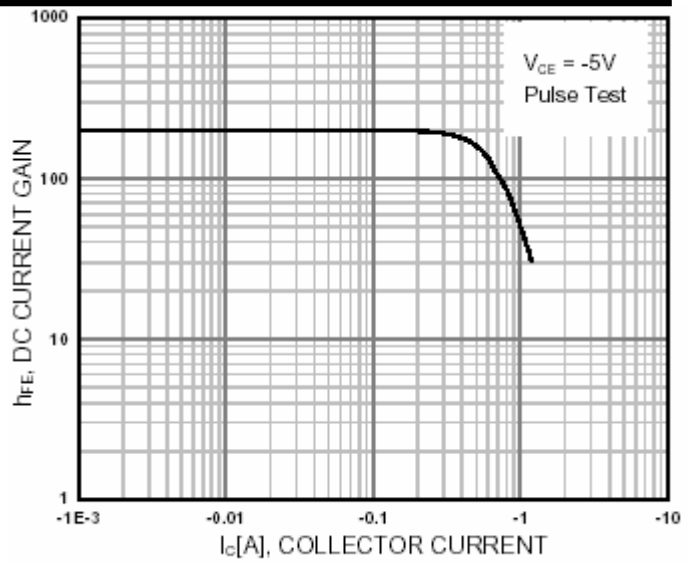


Fig.4 DC current Gain

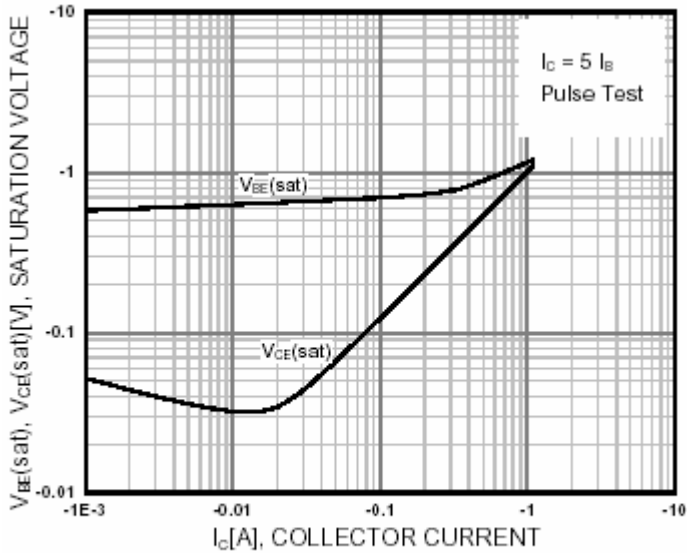


Fig.5 Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

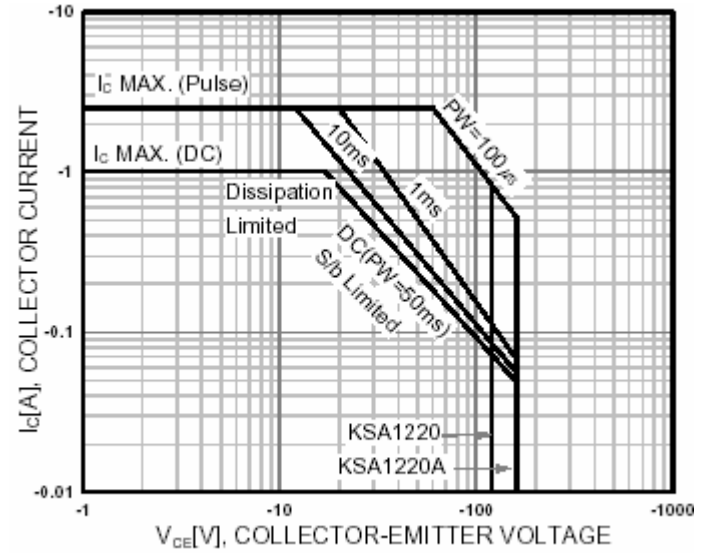


Fig.6 Safe Operating Area

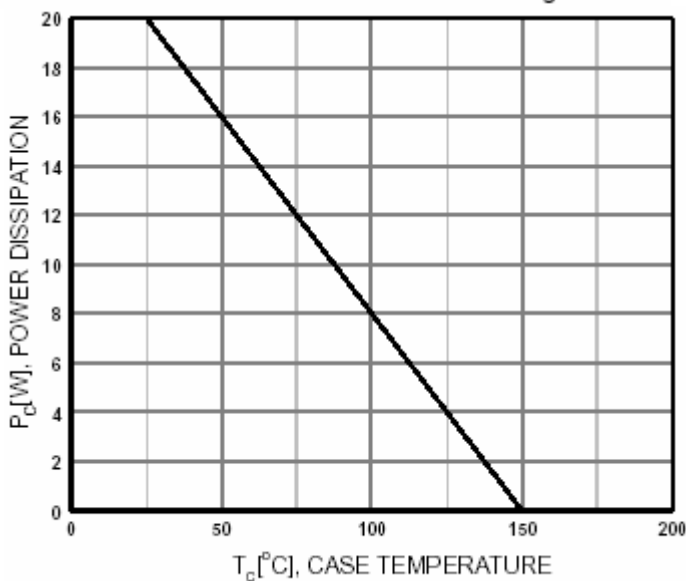


Fig.7 Power Derating